

NANO EXPRESS

Open Access



Low-Temperature Thermally Reduced Molybdenum Disulfide as a Pt-Free Counter Electrode for Dye-Sensitized Solar Cells

Che-Hsien Lin¹, Chuen-Horng Tsai¹, Fan-Gang Tseng^{1*}, Yang-Yen Yu², Hsuan-Chung Wu² and Chien-Kuo Hsieh^{2*}

Abstract

A two-dimensional nanostructure of molybdenum disulfide (MoS_2) thin film exposed layered nanosheet was prepared by a low-temperature thermally reduced (TR) method on a fluorine-doped tin oxide (FTO) glass substrate as a platinum (Pt)-free and highly electrocatalytic counter electrode (CE) for dye-sensitized solar cells (DSSCs). Thermogravimetric analysis (TGA) results show that the MoS_2 sulfidization temperature was approximately 300 °C. X-ray photoelectron spectroscopy (XPS), high-resolution transmission electron microscopy (HRTEM), and X-ray diffraction (XRD) indicate that the stoichiometry and crystallization of MoS_2 were more complete at higher temperatures; however, these temperatures reduce the number of edge-plane active sites in the short-range-order nanostructure. Accordingly, the DSSCs with 300 °C annealed TR- MoS_2 CE exhibited an excellent photovoltaic conversion efficiency (PCE) of 6.351 %, up to 91.7 % of which is obtained using the conventional TD-Pt CE (PCE = 6.929 %). The temperature of thermal reaction and the molar ratio of reaction precursors were found to significantly influence the resulting stoichiometry and crystallization of MoS_2 nanosheets, thus affecting DSSCs' performance.

Keywords: Molybdenum disulfide, Thermal reduction, Counter electrode, Dye-sensitized solar cells

Background

Since the first demonstration of dye-sensitized solar cells (DSSCs) by O'Regan and Grätzel [1], much attention has been paid to these third-generation solar cells due to their low cost, easy fabrication, high photo conversion efficiency, and environmental friendliness [2–5]. A DSSC typically comprises of a wide-band semiconductor (usually TiO_2) coated with dye molecules on a transparent conductive glass as a working electrode (WE), an electrolyte-containing iodide/triiodide (I^-/I_3^-) redox couple, and a counter electrode (CE), usually deposited platinum (Pt) on the transparent conductive glass. Pt is conventionally used as the CE catalyst in DSSCs to regenerate the electrolyte redox couple and collect electrons to complete the circuit. However, because the high cost and scarcity of Pt greatly restrict the commercial production of DSSCs,

the development of low-cost, good electrical conductivity, and high-electrocatalyst CE materials is highly desired to provide an economic solution for high-performance DSSCs.

Stimulated by the outstanding electrochemical activity of graphene, two-dimensional (2D) nanomaterials have attracted great attention in recent years [5–8]. Transition metal dichalcogenides (TMDCs), MX_2 , ($\text{M} = \text{Nb}, \text{Ta}, \text{Mo}, \text{W}$; $\text{X} = \text{S}, \text{Se}, \text{Te}$), have received much interest due to their 2D layered nanostructures, which are analogous to the graphene structure [9–11]. As a typical TMDC, the layer-dependent properties of molybdenum disulfide (MoS_2) have recently attracted considerable attention due to their great potential in the electrochemical fields of catalysis [9, 12], lithium-ion batteries [13–15], hydrogen evolution [9, 16, 17], and DSSCs [18, 19]. MoS_2 is composed of three stacked atomic layers (a Mo layer sandwiched between two S layers, S–Mo–S) and held together through van der Waals interactions [20].

However, MoS_2 tends to form zero-dimensional fullerene-like nanoparticles or one-dimensional nanotubes

* Correspondence: fangangtseng@gmail.com; jack_hsieh@mail.mcut.edu.tw

¹Department of Engineering and System Science, National Tsing Hua University, Hsinchu 30013, Taiwan, Republic of China

²Department of Materials Engineering, Ming Chi University of Technology, 84 Gungjuan Rd., Taishan District, New Taipei City 24301, Taiwan, Republic of China

during the synthetic process [21, 22]. Therefore, an efficient way to synthesize 2D layer-nanostructured MoS₂ is to use graphene or carbon nanotubes (CNTs) as a template substrate [10, 16, 18, 23]. Although significant efforts have been devoted to the preparation of 2D layer-nanostructured MoS₂, including scotch tape-based micromechanical exfoliation [24], liquid exfoliation [25–28], hydrothermal synthesis [14, 29], physical vapor deposition [30, 31], and chemical vapor deposition [32, 33], the easy synthesis of 2D layer-nanostructured MoS₂ at low temperatures by template-free approaches under mild conditions still remains a challenge [34, 35]. Additionally, the electrochemical activities of MoS₂ were correlated with the number of catalytically active edge sites [9, 12, 17, 36], for the reason that controlling the nanostructures with more edge sites at the atomic scale is an effective strategy to gain an effective MoS₂ catalyst. In this study, we produce an easy, thermally reduced (TR) MoS₂ nanosheet thin film on fluorine-doped tin oxide (FTO) glass at low temperature that provides the number of edge-plane active sites in the short-range-order nanostructure of MoS₂ nanosheets, and demonstrates good catalytic performance compared with conventional Pt CE DSSCs.

Methods

Preparations of the Molybdenum Disulfide Counter Electrodes

A FTO transparent glass (TEC-7, 2.2 mm, Hartford) substrate was ultrasonically cleaned sequentially in detergent, acetone (overnight), distilled water (DI water, 1 h), and ethanol (1 h). Ammonium tetrathiomolybdate ((NH₄)₂MoS₄) powder (ProChem Inc., 99.99 % purity; 0.8 g) was added to 20 mL of N,N-dimethylformide (DMF) to form a 4 wt% solution. The solution was then sonicated for 1 day before use [28]. Furthermore, the dispersed solution was coated on FTO glass by spin coating at 1600 rpm to control the thickness and flatness of the film. The substrate was then dried in air for 1 h and annealed in an H₂/Ar = 1:9 gas mixture at various temperatures for 45 min to obtain thermally reduced molybdenum sulfide (TR-MoS_x) samples. The annealing temperatures for the MoS₂ phase transformation in this study are 250, 300, and 350 °C. The thermally deposited platinum (TD-Pt) CE was prepared as a reference electrode by thermal reduction, which was carried out by dropping a H₂PtCl₆ isopropanol solution on an FTO glass substrate annealed at 450 °C for 20 min [37].

Fabrication of the TiO₂ Working Electrode

The working electrode utilized the same FTO glass coated with nanocrystalline TiO₂ using the print-screen method; the area and thickness of the TiO₂ film were about 0.28 cm² and 10 μm, respectively. The TiO₂ WE

was then gradually sintered to 550 °C in ambient air for 30 min before being slowly cooled at room temperature (RT). After calcination, the TiO₂ WE was then immersed in a N719 (Solaronix) solution (3 × 10⁻³ M in a 1:1 volumetric mixture of acetonitrile and *tert*-Butylalcohol) at RT for 24 h. Following the dye adsorption process, the dye-adsorbed TiO₂ WE was washed with acetonitrile to remove the remaining dye and dried at RT for a few seconds.

Fabrication of DSSC Devices

The efficiency of the TR-MoS_x CEs as well as the standard TD-Pt CE DSSC devices were quantitatively compared. The dye-adsorbed TiO₂ WE was future assembled with a CE into a sandwiched configuration and sealed with a 60-μm hot-melt surlyn (SX1170-60, Solaronix) by heating at 100 °C for a few seconds. The DSSC device was fabricated by drilling two holes on the CE and injecting an iodide-based electrolyte (AN-50, Solaronix) in the space between the electrodes after the assembling process. Finally, the holes on the CE were sealed after the electrolyte injection. DSSC devices were then illuminated by a class A quality solar simulator with a light intensity of 100 mW cm⁻² (AM 1.5), which was calibrated with a standard silicon cell.

Characterizations of Molybdenum Sulfide Counter Electrodes

In order to investigate the phase transformation and chemical states of the low-temperature thermally reduced MoS₂, thermogravimetric analysis (TGA) was conducted using a thermogravimetric analyzer (TGA Q50 V20.10 Build 36, USA) with a heating rate of 5 °C min⁻¹ in ambient Nitrogen. X-ray photoelectron spectroscopy (XPS) was conducted using a PHI Quantera SXM/AES 650 (ULVAC-PHI INC., Japan.) equipment with a hemispherical electron analyzer and a scanning monochromated Al Kα (hν = 1486.6 eV) X-ray source to study the chemical states of Mo and S of the prepared MoS_x annealing samples. The XPS curve-fitting program, XPSPEAK 4.1, was used for peak de-convolution and assignment of binding energies, which was referenced to the adventitious C1s peak at 284.6 eV. For spectrum analysis, the background signal was subtracted by Shirley's method, and the curve fitting was performed by using a Gaussian–Lorentzian peak after Shirley background correction. Raman spectra were collected with a confocal micro-Raman spectroscopy (LABRAM HR 800 UV, Japan) using a 514-nm Ar⁺ laser source with a spot size of approximately 1 μm. The surface morphology of the prepared MoS_x annealing samples was examined by using the field emission scanning electron microscope (FESEM, JEOL, JSM-6330F, Japan). The nanostructures of MoS₂ were examined by using the transmission electron microscope (TEM, JEOL-2100F, Japan) equipped with EDS to determine the elements

contained in the samples. X-ray diffraction (XRD, PANalytical-X'Pert PRO MPD) with a $\text{CuK}\alpha$ radiation of 0.1541 nm was used to determine the crystallinities of the films.

According to our previous studies [3, 4], cyclic voltammetry (CV) measurements and the electrochemical impedance spectroscopy (EIS) were carried out to examine electrochemical properties. CV measurements were used to measure electrochemical redox ability using a potentiostat/galvanostat (PGSTAT 302N, Autolab, Eco Chemie, Netherlands) in a three-electrode configuration. Platinum wire and an Ag/AgCl electrode were used as the counter and reference electrodes, respectively. The solution used for CV measurements contained 1 mM I_2 , 10 mM LiI, and 0.1 M LiClO_4 in acetonitrile. EIS spectra were obtained using the aforementioned potentiostat/galvanostat equipped with a frequency response analysis (FRA) module; EIS results were analyzed using an equivalent circuit model with Autolab FRA software (v4.9, EcoChemie B.V.). The frequencies used in the scan ranged from 10^6 to 10^{-2} Hz, and an applied voltage of 10 mV was used.

In addition, Tafel polarization measurements were carried out using the potentiostat/galvanostat equipped with a linear polarization module to examine the electrocatalytic activity at the electrolyte–electrode interface. Both EIS and Tafel polarization measurements were obtained using symmetrical devices in the dark.

The photocurrent–voltage characteristics of DSSC devices were measured under simulated solar illumination (AM 1.5, 100 mW cm^{-2} , Oriel 91160, Newport Corporation, USA), equipped with an AM 1.5G filter (Oriel 81088A, Newport Corporation, USA) and a 300-W xenon lamp (Oriel 6258, Newport Corporation, USA). The simulated incident light intensity was calibrated using a reference Si cell (calibrated at NREL, PVM-81).

Results and Discussion

Composition and Morphologies

In this study, our homemade CVD system served as an important tool for the TR- MoS_x annealing at low temperatures. TGA curves for the three complexes, $(\text{NH}_4)_2\text{MoS}_4$, 4 wt% $(\text{NH}_4)_2\text{MoS}_4$ in DMF, and pure MoS_2 powder, as shown in Fig. 1, were analyzed to identify the MoS_2 sulfidization temperature region. Quantitative data derived from the TGA curves are summarized in Table 1. As we can see from curve (a) in Fig. 1, the $(\text{NH}_4)_2\text{MoS}_4$ monomer decomposition was similar to a previous report [38]; there are two TGA regions in curve (a). The first is a sharp step from RT to 200 °C that corresponds to the loss of ammonia and hydrogen sulfide according to the following reaction:

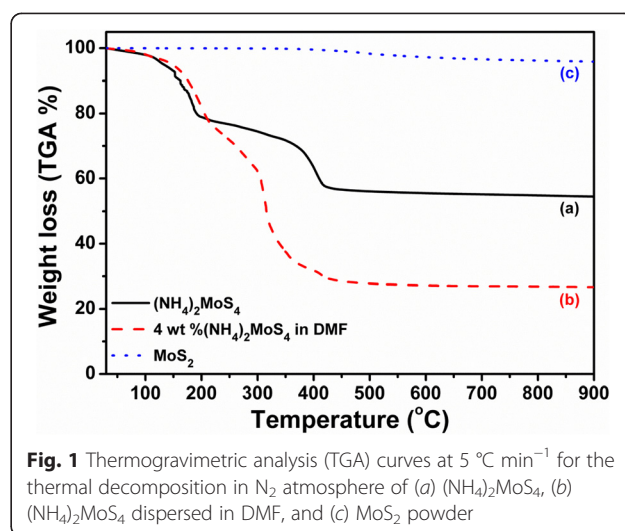
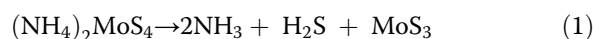
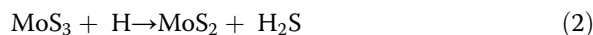


Fig. 1 Thermogravimetric analysis (TGA) curves at $5\text{ }^\circ\text{C min}^{-1}$ for the thermal decomposition in N_2 atmosphere of (a) $(\text{NH}_4)_2\text{MoS}_4$, (b) $(\text{NH}_4)_2\text{MoS}_4$ dispersed in DMF, and (c) MoS_2 powder



The second decomposition occurs from 200 to 420 °C, indicating the MoS_2 phase transformation according to Eq.(2).



The $(\text{NH}_4)_2\text{MoS}_4$ precursor dispersed in DMF was also analyzed by TGA (curve (b) in Fig. 1); the most weight loss occurs in the temperature range from 220 °C to 450 °C, which also indicates the MoS_2 phase transformation. Commercial MoS_2 powder was also used as a reference (curve (c) in Fig. 1) that shows a broad temperature region (RT to 900 °C) and great thermal stability [39]. For future study, we carried out the three annealing conditions in our homemade furnace thermal CVD in H_2 mixed gas ($\text{H}_2/\text{Ar} = 1:9$) at 350, 300, and 250 °C.

In this study, we focused on the non-stoichiometric chemical compositions of TR- MoS_x thin films in different temperature regions; the relationship of temperature with the performance was studied by XPS at various temperatures. Figure 2 shows the XPS spectrum of the TR- MoS_x samples annealed at 350, 300, and 250 °C; the left side and right side of Fig. 2 show the chemical states of Mo 3d and S 2p orbitals, respectively. The peak positions, intensities (atomic percentage), and the stoichiometric ratio (S/Mo) are also given in Table 2.

The TR- MoS_x annealed at 350 °C exhibits two main peaks of Mo 3d spectra at 229.22 and 232.36 eV that correspond to $\text{Mo}^{4+} 3d_{5/2}$ and $\text{Mo}^{4+} 3d_{3/2}$ orbitals, revealing that the Mo^{4+} state is dominant in the 350 °C annealed sample and indicating the formation of MoS_2 [12]. Additional peaks are observed at 162.05 and 163.24 eV, which correspond to the known S $2p^{2-}_{3/2}$ and S $2p^{2-}_{1/2}$ MoS_2 doublet peaks, respectively [12].

Table 1 Thermal analysis data for the thiomolybdates decomposition in N₂

Compound	TG region	Temperature range (°C)	Probable product	Experimental weight loss (%)
(NH ₄) ₂ MoS ₄	1	RT –200	MoS ₃	21.08
	2	200–900	MoS ₂	45.50
(NH ₄) ₂ MoS ₄ + DMF	1	RT –225	MoS ₃ (+DMF)	24.51
	2	225–900	MoS ₂	73.31
MoS ₂	1	RT –900	MoS ₂	<1

The stoichiometric ratio (S/Mo) quantified by relative sensitivity factors (RSF) from the respective integrated peak area of XPS spectra is close to 2.03, also indicating that the structure of the 350 °C annealed sample is MoS₂. Whereas the annealing temperature is lowered to 250 °C, in addition to that the XPS peaks of the MoS₂ structure, other deconvoluted peaks need the concern. The peaks at 230.18 eV (Mo⁵⁺ 3d_{5/2}) and 233.32 eV (Mo⁵⁺ 3d_{3/2}), 231.40 eV (Mo⁶⁺ 3d_{5/2}) and 234.54 eV (Mo⁶⁺ 3d_{3/2}), 232.50 eV (Mo⁶⁺ 3d_{5/2}) and 235.64 eV (Mo⁶⁺ 3d_{3/2}), representing the Mo 3d_{5/2} and Mo 3d_{3/2} of the three valence states can be assigned to Mo₂S₅, MoS₃, and MoO₃, respectively [12, 40, 41]. Meanwhile, the binding energy at 163.20 eV (S₂²⁻ 2p_{3/2}) and 164.39 eV (S₂²⁻ 2p_{1/2}) might represent to the intermediate product of Mo₂S₅

and the MoS₃ with a formula of [Mo⁴⁺ (S₂)²⁻S²⁻] [42, 43]. It is worthwhile to mention that the MoS₂ fraction decrement is nearly linear with annealing temperature down to 250 °C, and it becomes gradual at lower temperatures. These results suggest an incomplete MoS₂ phase transformation at lower annealing temperature, which is consistent with our TGA results. The stoichiometric ratio (S/Mo) estimated from the 250 and 300 °C annealing sample were 2.26 and 2.19, respectively. In addition, compared with the 250 °C annealing sample, note that the line width of MoS₂ peaks becomes progressively stronger and narrower for annealing temperatures above 300 °C.

The Raman spectrums of the synthesized samples are shown in Fig. 3. All annealing samples showed the two

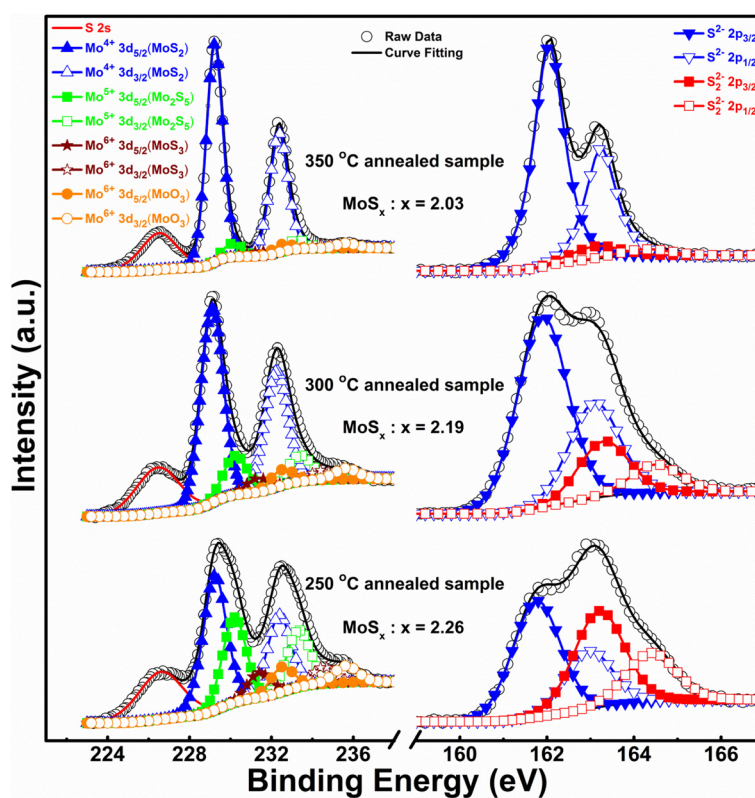
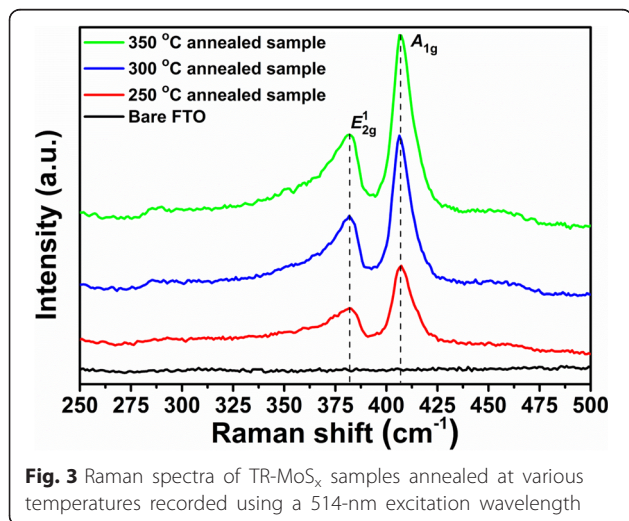
**Fig. 2** The Mo 3d and S 2p peak in the XPS spectra of the TR-MoS_x annealed at 350, 300, and 250 °C

Table 2 The Mo 3d and S 2p peak positions, atomic percentages, and x values of the TR-MoS_x samples annealed at 250, 300, and 350 °C

Peak and identity		Fitting of Mo 3d and S 2p peak binding energy (eV) (atomic percentage (%))		
		250 °C	300 °C	350 °C
Mo ⁴⁺ 3d _{5/2}	MoS ₂	229.23(31.2)	229.10(44.4)	229.22(54.0)
Mo ⁴⁺ 3d _{3/2}		232.37(18.1)	232.24(27.6)	232.36(32.6)
Mo ⁵⁺ 3d _{5/2}	Mo ₂ S ₅	230.18(19.2)	230.23(9.7)	230.10(4.2)
Mo ⁵⁺ 3d _{3/2}		233.32(12.8)	233.37(6.4)	233.24(2.8)
Mo ⁶⁺ 3d _{5/2}	MoS ₃	231.40(5.6)	231.30(3.4)	231.40(1.7)
Mo ⁶⁺ 3d _{3/2}		234.54(3.8)	234.44(2.3)	234.54(1.1)
Mo ⁶⁺ 3d _{5/2}	MoO ₃	232.50(5.6)	232.50(3.7)	232.50(2.2)
Mo ⁶⁺ 3d _{3/2}		235.64(3.8)	235.64(2.5)	235.64(1.5)
S ²⁻ 2p _{3/2}	MoS ₂	161.76(35.7)	161.90(51.8)	162.05(61.7)
S ²⁻ 2p _{1/2}		162.95(17.9)	163.09(25.9)	163.24(30.9)
S ₂ ²⁻ 2p _{3/2}	-	163.20(30.9)	163.30(14.9)	163.10(4.9)
S ₂ ²⁻ 2p _{1/2}		164.39(15.5)	164.49(7.4)	164.29(2.5)
S/Mo ratio (x values)		2.26	2.19	2.03

prominent Raman peaks of MoS₂ at about 381 cm⁻¹ (E_{2g}^1) and 406 cm⁻¹ (A_{1g}) [44]. The E_{2g}^1 mode corresponds to the in-plane vibration from two S atoms with respect to the Mo atom in opposite vibration; the A_{1g} mode is associated with the out-of-plane vibration of only S atoms along the plane directions [45]. In addition, the observation of E_{2g}^1 and A_{1g} Raman peaks at 381 and 406 cm⁻¹ suggested the presence of multi-layered MoS₂ nanosheets [44, 45]. Meanwhile, the peak intensity and full width at half maximum (FWHM) of MoS₂ becomes stronger and narrower as the annealing temperature up to 300 °C, that suggested the complete and genuine MoS₂ structure.

Figure 4 shows the SEM images that correspond to the bare FTO substrate and the TR-MoS_x samples

**Fig. 3** Raman spectra of TR-MoS_x samples annealed at various temperatures recorded using a 514-nm excitation wavelength

annealed at 250, 300, and 350, respectively. Obviously, all the prepared TR-MoS_x electrodes showed the film-like morphology on the surface of FTO substrate, which was prepared by spin coating technology and controlled the flatness of the film.

Figure 5 shows high-resolution transmission electron microscopy (HRTEM) images and the corresponding selected area electron diffraction (SAED) of the annealed samples at 250, 300, and 350 °C. Figure 5a, d shows the HRTEM image and SAED of the MoS_x annealed at 250 °C, respectively. Because the major phase is MoS₃ at 250 °C, we can confirm that the MoS₃ synthesized at this temperature is noncrystalline, which is consistent with a previous report [18]. Fig. 5b shows the separated layer-nanostructured MoS₂, formed after the MoS₃ was converted to crystallized MoS₂ at 300 °C. The lateral size of the crystal domain in the independent MoS₂ nanosheets is approximately few nanometers, corresponding to 3–5 layers as seen in Fig. 5b; Fig. 5e shows the SAED of Fig. 5b. These short-range-order structure of MoS₂ nanosheets played a number of important roles: (i) the edge-planes of the MoS₂ nanosheet structure provided a large number of active sites for redox reactions [12], (ii) the separation and independence of the MoS₂ nanosheet allowed the I₃⁻ ions to easily diffuse to the active sites of the edge-planes for the reduction reaction, and (iii) the independent MoS₂ nanosheets increased the specific surface area available to promote the charge-transfer rate. Accordingly, the interlayer distance of the MoS₂ nanosheets in this study was about 6 Å; this distance corresponds to the spacing between the (002) basal planes of MoS₂, similar to a previous study [15, 45]. Fig. 5c, f show the HRTEM image and SAED of MoS_x annealed at 350 °C, respectively.

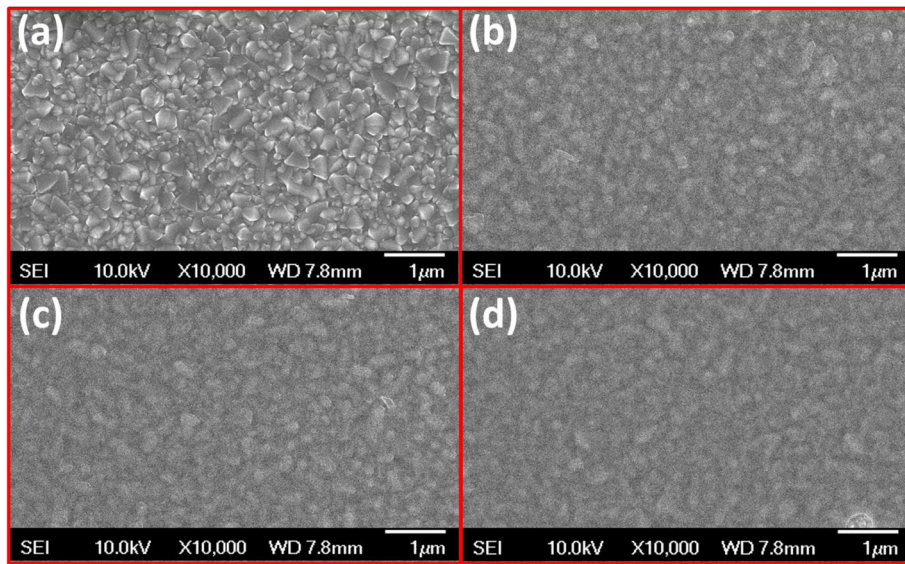


Fig. 4 The SEM images of the **a** bare FTO and the TR-MoS_x samples annealed at **b** 250, **c** 300, and **d** 350 °C, respectively

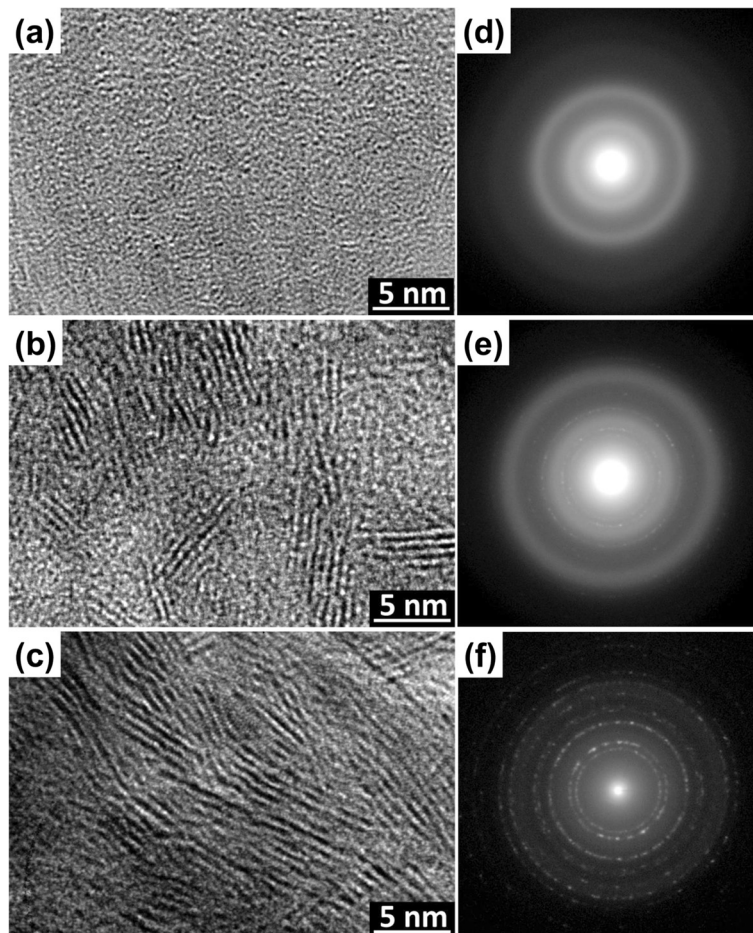


Fig. 5 **a–c** TEM images of the TR-MoS_x annealed at 250, 300, and 350 °C and **d–f** the corresponding diffraction patterns, respectively

The structure of the MoS₂ nanosheets becomes more complete and reduces the number of the edge-planes of the MoS₂ nanosheets, as shown in Fig. 5c. Due to this short-range-order structure, fewer edge-planes of active sites can be used in the redox reactions. By comparing Fig. 5f, e with the HRTEM images at different annealing temperatures and their corresponding SAED patterns, we can determine whether the MoS₂ crystallization was more complete at higher temperature. To further confirm the identity and structure of the annealed sample, XRD measurements were carried out. Figure 6 shows the XRD pattern of the TR-MoS_x samples annealed at 350, 300, and 250 °C, respectively. The diffraction peak (#) of (002) that comes from the basal planes of MoS₂ can be observed. On the other hand, compared with the 250 °C annealed sample, the peak intensity and FWHM of MoS₂ become more stronger and narrower as the annealing temperature reach to 300 °C; it suggested that the MoS₂ crystallization was more complete at higher temperature. From the TEM and XRD results, it is noted that the layered MoS₂ nanosheet thin films synthesized on FTO with sulfurization are actually polycrystalline when the annealing temperature exceeds 300 °C; the grain growth occurred at 350 °C to form the long-range-order MoS₂ nanosheets.

Electrocatalytic Properties

In order to estimate the electrocatalytic performance of the TR-MoS_x toward I₃⁻ reduction, CV analysis was performed using a potential interval ranging from -0.4 to 1.0 vs Ag/AgCl and a scan rate of 50 mV s⁻¹. Figure 7a shows the results of the CV measurements in the I⁻/I₃⁻ system based on the TD-Pt CE and TR-MoS_x CEs annealed at 250 °C, 300 °C and 350 °C. Typically, there are two pairs of redox peaks in the cyclic voltammogram. The relatively positive pair (Ox (i) and Red (i))

corresponds to the redox of I₂/I₃⁻ (Eq. (3)). The other pair (Ox (ii) and Red (ii)) is associated with the redox of I₃⁻/I⁻, as presented in Eq. (4).



The anodic peak current (*I*_{pa}) and the cathodic peak current (*I*_{pc}) corresponded to the oxidation of I⁻ ions and the reduction of I₃⁻ ions, respectively. The magnitude of *I*_{pc} corresponded to the catalytic activation of a C.E. for I₃⁻ reduction in a DSSC [3]. In addition, the peak to peak voltage separation between the anodic and the cathodic peaks (*E*_{pp}) can be considered to the redox barrier of I₃⁻/I⁻ redox couples. Therefore, the higher *I*_{pc} and lower *E*_{pp} values means the better electrocatalytic activity of CEs in DSSC [19]. From Fig. 7 (a), it can be observed that the TD-Pt and TR-MoS_x CEs exhibit two redox pairs, whereas no significant peak is observed when the annealing temperature is below 300 °C. This indicates that our TR-MoS_x annealed at 300 °C exhibits similar electrocatalytic activity to the TD-Pt CE, while the noncrystalline TR-MoS_x CE annealed at 250 °C provides poor electrocatalytic activity. Furthermore, the current density of the redox peaks for the TR-MoS_x CE annealed at 300 °C is higher than those annealed at 250 and 350 °C. In other words, compared to the other conditions, the 300 °C annealed sample can exhibit the highest *I*_{pc} and lowest *E*_{pp} that toward the best I₃⁻ ion electrochemical reduction performance.

To further investigate the electrocatalytic properties, EIS was carried out using symmetrical cells comprising two identical TD-Pt CEs and various TR-MoS_x CEs annealed at 250, 300, and 350 °C, as shown in Fig. 7b. The corresponding EIS parameters obtained from a Nyquist plot are summarized in Table 3, in which *R*_s corresponds to the series resistance of the electrolyte and electrodes and *R*_{ct} is the charge-transfer resistance at the electrolyte–electrode interface. From Fig. 7b and Table 3, the *R*_{ct} values for the TD-Pt CE and the TR-MoS_x CEs annealed at 300 and 350 °C are 14.98, 30.98, and 141.41 Ω cm², respectively; no *R*_{ct} value is identified for MoS_x annealed at 250 °C because the *R*_{ct} was too big to fit. We herein suggest that the noncrystalline MoS₃ (annealed at 250 °C) exhibits a poor conductivity due to insufficient energy for sulfurization to produce MoS₂, which is consistent with CV results (Fig. 7a).

Tafel polarization measurements were used to examine the exchange current density (*J*₀) at the electrolyte–catalyst interface (shown in Fig. 7c). The tangential slope of the Tafel curve provides information about the exchange current density (linear segments extrapolate to an intercept of log *J*₀), which is closely associated with the *R*_{ct} value (Eq. (5)) [19]. As we can see in Fig. 7c, the 300 °C

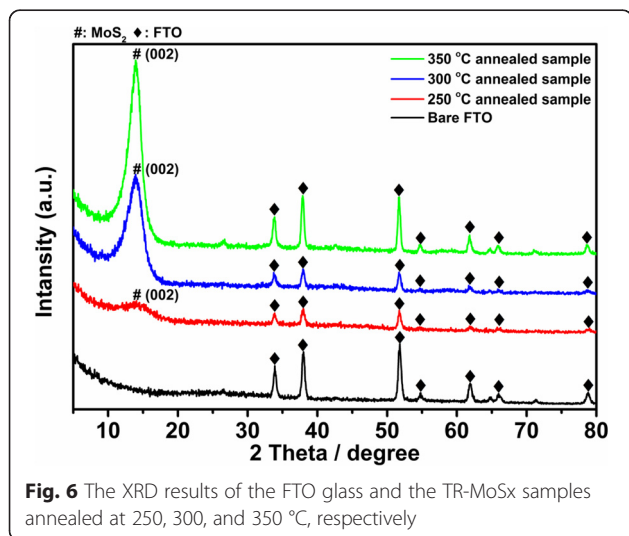
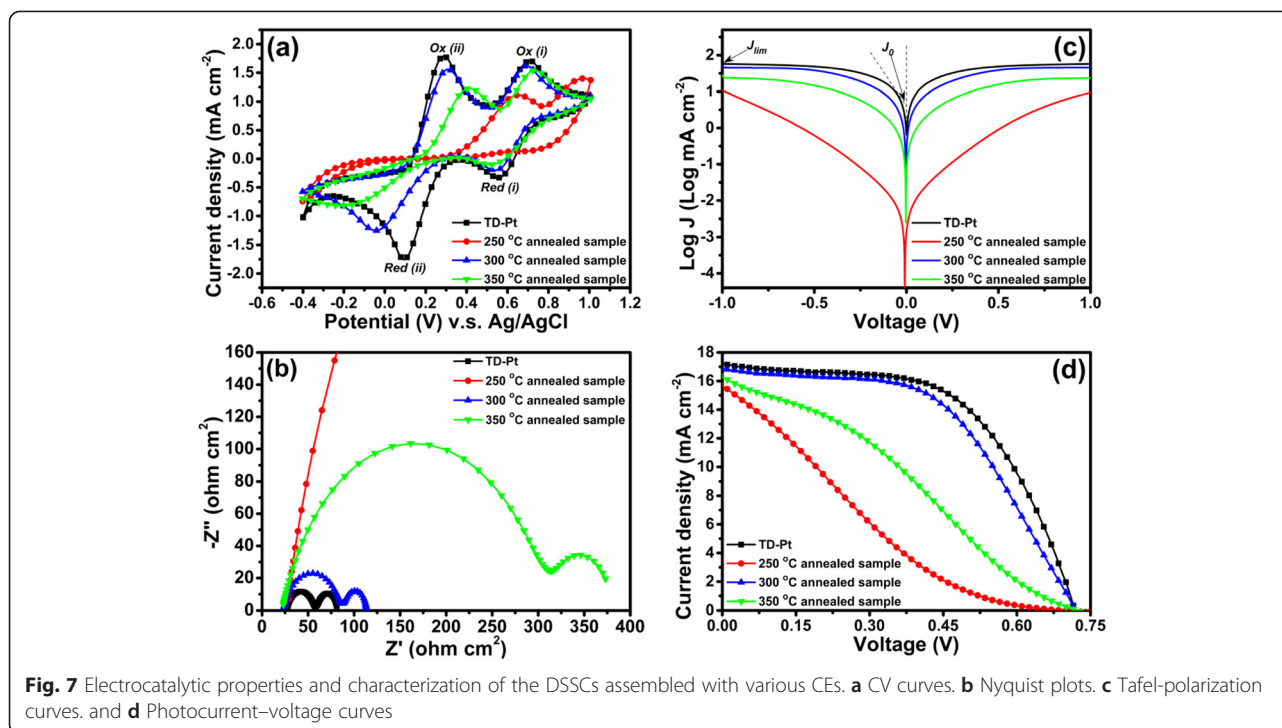


Fig. 6 The XRD results of the FTO glass and the TR-MoS_x samples annealed at 250, 300, and 350 °C, respectively



annealed TR-MoS_x electrode has a large exchange current density (J_0) compared with the 250 and the 350 °C annealed samples and was comparable with the TD-Pt electrode (summarized in Table 3), which means higher electrocatalytic activity and lower charge–transfer resistance at the electrolyte–electrode interface.

Photovoltaic Performance of DSSCs

As shown in Fig. 7d, the photovoltaic performance of DSSCs is characterized using the short-circuit current density (J_{sc}), open-circuit voltage (V_{oc}), fill factor (FF), and photoconversion efficiency (η); these parameters are summarized in Table 3. The J_{sc} , V_{oc} , and FF of the DSSC with a reference TD-Pt film CE were 17.056 mA cm⁻², 0.724 V, and 0.557, respectively, yielding a photoconversion efficiency of 6.929 %. The DSSC with the TR-MoS_x CE annealed at 300 °C exhibits a higher conversion efficiency (6.351 %) compared with those prepared at other annealing temperatures; the corresponding J_{sc} , V_{oc} , and FF were 16.905 mA cm⁻², 0.727 V, and 0.517, respectively, which

agreed with the CV and EIS measurements. It is worth noting that the values of J_{sc} for the TR-MoS₂ CEs annealed at 250 and 350 °C were 15.442 and 16.063 mA cm⁻², respectively.

As we can see, Tafel-polarization measurements (Fig. 7c) are consistent with the EIS results (showed in Fig. 7b) because J_0 is inversely proportional to R_{ct} (Eq. (5)). The lower charge–transfer resistance (R_{ct}) at the electrolyte–electrode interface reduces the loss during charge transportation and enhances charge collection efficiency, increasing the photocurrent (J_{sc}) and FF of DSSCs.

$$J_0 = \frac{RT}{nFR_{ct}} \quad (5)$$

From Fig. 7c, the TR-MoS₂ electrode annealed at 300 °C also possesses the largest limiting current density (J_{lim}), which depends on the diffusion

Table 3 Photovoltaic parameters of the DSSCs based on various CEs and electrochemical parameters from EIS and Tafel measurements

Counter electrode	R_s/Ω cm ²	R_{ct}/Ω cm ²	$J_0/\text{mA cm}^{-2}$	$J_{sc}/\text{mA cm}^{-2}$	V_{oc}/V	FF	$\eta(\%)$
TD-Pt film	27.17	14.98	4.78	17.056 ± 0.075	0.724 ± 0.003	0.557 ± 0.007	6.929 ± 0.063
250 °C annealed sample	28.58	–	0.01	15.442 ± 0.118	0.709 ± 0.004	0.175 ± 0.002	1.917 ± 0.026
300 °C annealed sample	23.89	30.98	2.54	16.905 ± 0.013	0.727 ± 0.003	0.517 ± 0.005	6.351 ± 0.045
350 °C annealed sample	23.13	141.41	0.54	16.063 ± 0.251	0.725 ± 0.005	0.299 ± 0.005	3.479 ± 0.101

coefficient of the I^-/I_3^- redox couple in the DSSC according to Eq. (6) [19].

$$D = \frac{l}{2nFC} J_{\text{lim}} \quad (6)$$

where R is the gas constant, D is the diffusion coefficient of the triiodide, l is the spacer thickness, and F and n have their normal meanings. In other words, EIS and Tafel results explain the good photovoltaic performance of DSSCs based on the TR-MoS₂ CE annealed at 300 °C.

The values of J_{sc} and FF can be considered indicative of the number of edge-plane active sites for redox reactions[3]. Although the crystallization of MoS₂ was more complete at higher temperature, the J_{sc} and FF of TR-MoS_x annealed at 350 °C ($J_{\text{sc}} = 16.063$, FF = 0.299) are smaller than those of the TR-MoS_x annealed at 300 °C ($J_{\text{sc}} = 16.905$, FF = 0.517). Here, we suggest that the long-range-order nanostructure of the 350 °C annealed MoS₂ reduces the active sites of the edge-planes.

In summary, the independent MoS₂ nanosheets annealed at 300 °C provide the best electrocatalytic activity toward I₃⁻ reduction. CV, EIS, and Tafel measurements suggest that the 300 °C annealing temperature should generate a larger active area. This results an excellent photovoltaic conversion efficiency (PCE) of 6.351 % under AM 1.5 illumination of 100 mW cm⁻², up to 91.7 % of which is obtained using the conventional TD-Pt CE (PCE = 6.929 %). These results demonstrate that the 300 °C annealed TR-MoS₂ CE has a great potential as a low-cost alternative to Pt in DSSCs.

Conclusions

In this work, a two-dimensional nanostructure of MoS₂ has been successfully synthesized by a low temperature TR method on FTO glass substrates. This material was also incorporated into a Pt-free DSSC for application. In the TGA results, it was found that the MoS₂ sulfidization temperature was approximately 300 °C which provided the effective MoS₂ phase transformation process. Additionally, XPS, TEM, and XRD indicate that the stoichiometry and crystallization of MoS₂ were more complete at higher temperatures; however, these temperatures reduce the number of edge-plane active sites in the short-range-order nanostructure. The electrochemical analysis also showed that the 300 °C annealed TR-MoS₂ CE provided an independent nanosheet nanostructure with numerous active sites that demonstrated Pt-like electrocatalytic activity for I₃⁻ reduction. These short-range-order nanostructure of MoS₂ nanosheets provided a great of edge-plane active sites to enhance the catalytic performance to increase the J_{sc} and FF, and an outstanding PCE can be obtained. Accordingly, the DSSC assembled with the 300 °C annealed TR-MoS₂ structure exhibited an

excellent PCE of 6.351 %; up to 91.7 % of which is obtained using the conventional TD-Pt CE (PCE = 6.929 %). This leads us to the conclusion that the low temperature TR-MoS₂ CE is a promising candidate for application as a highly efficient and low-cost CE material in Pt-free DSSCs.

Competing Interests

The authors declare that they have no competing interests.

Authors' Contributions

CHL designed the methods and experiments, carried out the laboratory experiments, analyzed the data, interpreted the results, and wrote the paper. FGT, CHT, HCW, and CKH worked together on developing the conceptual framework and supervised the work. YYY supported the TGA analysis and discussion. All authors have contributed to the revision of the manuscript and have read and approved the final manuscript.

Authors' Information

CHL is PhD program student at National Tsing Hua University. FGT holds a professor position at National Tsing Hua University. CHT holds a professor position at National Tsing Hua University. YYY holds a professor position at Ming Chi University of Technology. HCW holds an associate professor position at Ming Chi University of Technology. CKH holds an assistant professor position at Ming Chi University of Technology.

Acknowledgements

The financial support provided by the Ministry of Science and Technology of Taiwan through Project: MOST 103-2221-E-131 -029 is greatly appreciated.

Received: 27 August 2015 Accepted: 11 November 2015

Published online: 17 November 2015

References

- O'Regan B, Gratzel M (1991) A low-cost, high-efficiency solar-cell based on dye-sensitized colloidal TiO₂ films. *Nature* 353:737
- Gratzel M (2001) Photoelectrochemical cells. *Nature* 414:338
- Hsieh CK, Tsai MC, Su CY, Wei SY, Yen MY, Ma CCM et al (2011) A hybrid nanostructure of platinum-nanoparticles/graphitic-nanofibers as a three-dimensional counter electrode in dye-sensitized solar cells. *Chem Commun* 47:11528
- Hsieh CK, Tsai MC, Yen MY, Su CY, Chen KF, Ma CCM et al (2012) Direct synthesis of platelet graphitic-nanofibres as a highly porous counter-electrode in dye-sensitized solar cells. *Phys Chem Phys* 14:4058
- Chang LH, Hsieh CK, Hsiao MC, Chiang JC, Liu PI, Ho KK et al (2013) A graphene-multi-walled carbon nanotube hybrid supported on oxide as a counter electrode of dye-sensitized solar cells. *J Power Sources* 222:518
- Zhang L, Zhang F, Yang X, Long GK, Wu YP, Zhang TF et al (2013) Porous 3D graphene-based bulk materials with exceptional high surface area and excellent conductivity for supercapacitors. *Sci Rep* 3:1408
- Hu LH, Wu FY, Lin CT, Khlobystov AN, Li LJ (2013) Graphene-modified LiFePO₄ cathode for lithium ion battery beyond theoretical capacity. *Nat Commun* 4:1687
- Yoo EZhou HS (2013) Fe phthalocyanine supported by graphene nanosheet as catalyst in Li-air battery with the hybrid electrolyte. *J Power Sources* 244:429
- Karunadasa HI, Montalvo E, Sun YJ, Majda M, Long JR, Chang CJ (2012) A molecular MoS₂ edge site mimic for catalytic hydrogen generation. *Sci* 335:698
- Roy K, Padmanabhan M, Goswami S, Sai TP, Ramalingam G, Raghavan A et al (2013) Graphene-MoS₂ hybrid structures for multifunctional photoresponsive memory devices. *Nat Nanotechnol* 8:826
- Wang QH, Kalantar-Zadeh K, Kis A, Coleman JN, Strano MS (2012) Electronics and optoelectronics of two-dimensional transition metal dichalcogenides. *Nat Nanotechnol* 7:699
- Kibsgaard J, Chen ZB, Reinecke BN, Jaramillo TF (2012) Engineering the surface structure of MoS₂ to preferentially expose active edge sites for electrocatalysis. *Nat Mater* 11:963

13. Pham VH, Kim KH, Jung DW, Singh K, Oh ES, Chung JS (2013) Liquid phase co-exfoliated MoS₂-graphene composites as anode materials for lithium ion batteries. *J Power Sources* 244:280
14. Yang LC, Wang SN, Mao JJ, Deng JW, Gao QS, Tang Y, Schmidt OG (2013) Hierarchical MoS₂/polyaniline nanowires with excellent electrochemical performance for lithium-ion batteries. *Adv Mater* 25:1180
15. Sun PL, Zhang WX, Hu XL, Yuan LX, Huang YH (2014) Synthesis of hierarchical MoS₂ and its electrochemical performance as an anode material for lithium-ion batteries. *J Mater Chem A* 2:3498
16. Firmiano EGS, Cordeiro MAL, Rabelo AC, Dalmaschio CJ, Pinheiro AN, Pereira EC et al (2012) Graphene oxide as a highly selective substrate to synthesize a layered MoS₂ hybrid electrocatalyst. *Chem Commun* 48:7687
17. Jaramillo TF, Jorgensen KP, Bonde J, Nielsen JH, Horch S, Chorkendorff I (2007) Identification of active edge sites for electrochemical H₂ evolution from MoS₂ nanocatalysts. *Science* 317:100
18. Tai SY, Liu CJ, Chou SW, Chien FSS, Lin JY, Lin TW (2012) Few-layer MoS₂ nanosheets coated onto multi-walled carbon nanotubes as a low-cost and highly electrocatalytic counter electrode for dye-sensitized solar cells. *J Mater Chem* 22:24753
19. Al-Mamun M, Zhang HM, Liu PR, Wang Y, Cao HJ, Zhao J (2014) Directly hydrothermal growth of ultrathin MoS₂ nanostructured films as high performance counter electrodes for dye-sensitized solar cells. *Rsc Adv* 4:21277
20. Benavente E, Santa Ana MA, Mendizabal G, Gonzalez F (2002) Intercalation chemistry of molybdenum disulfide. *Coord Chem Rev* 224:87
21. Seayad A, Antonelli DM (2004) Recent advances in hydrogen storage in metal-containing inorganic nanostructures and related materials. *Adv Mater* 16:765
22. Matte HSSR, Gomathi A, Manna AK, Late DJ, Datta R, Pati SK et al (2010) MoS₂ and WS₂ analogues of graphene. *Angew Chem Int Ed* 49:4059
23. Shi YM, Zhou W, Lu AY, Fang WJ, Lee YH, Hsu AL et al (2012) van der Waals epitaxy of MoS₂ layers using graphene as growth templates. *Nano Lett* 12:2784
24. Radisavljevic B, Radenovic A, Brivio J, Giacometti V, Kis A (2011) Single-layer MoS₂ transistors. *Nat Nanotechnol* 6:147
25. Zhou KG, Mao NN, Wang HX, Peng Y, Zhang HL (2011) A mixed-solvent strategy for efficient exfoliation of inorganic graphene analogues. *Angew Chem Int Ed* 50:10839
26. Tang ZH, Wei QY, Guo BC (2014) A generic solvent exchange method to disperse MoS₂ in organic solvents to ease the solution process. *Chem Commun* 50:3934
27. Wang YC, Ou JZ, Balendhran S, Chrimes AF, Mortazavi M, Yao DD et al (2013) Electrochemical control of photoluminescence in two-dimensional MoS₂ nanoflakes. *ACS Nano* 7:10083
28. Coleman JN, Lotya M, O'Neill A, Bergin SD, King PJ, Khan U et al (2011) Two-dimensional nanosheets produced by liquid exfoliation of layered materials. *Sci* 331:568
29. Huang GC, Chen T, Chen WX, Wang Z, Chang K, Ma L et al (2013) Graphene-like MoS₂/graphene composites: cationic surfactant-assisted hydrothermal synthesis and electrochemical reversible storage of lithium. *Small* 9:3693
30. Lauritsen JV, Kibsgaard J, Helveg S, Topsoe H, Clausen BS, Laegsgaard E et al (2007) Size-dependent structure of MoS₂ nanocrystals. *Nat Nanotechnol* 2:53
31. Helveg S, Lauritsen JV, Laegsgaard E, Stensgaard I, Nørskov JK, Clausen BS et al (2000) Atomic-scale structure of single-layer MoS₂ nanoclusters. *Phys Rev Lett* 84:951
32. Liu KK, Zhang WJ, Lee YH, Lin YC, Chang MT, Su C et al (2012) Growth of large-area and highly crystalline MoS₂ thin layers on insulating substrates. *Nano Lett* 12:1538
33. Lee YH, Zhang XQ, Zhang WJ, Chang MT, Lin CT, Chang KD et al (2012) Synthesis of large-area MoS₂ atomic layers with chemical vapor deposition. *Adv Mater* 24:2320
34. Shi ZW, Lu H, Liu Q, Cao FR, Guo J, Deng KM et al (2014) Efficient p-type dye-sensitized solar cells with all-nano-electrodes: NiCo₂S₄ mesoporous nanosheet counter electrodes directly converted from NiCo₂O₄ photocathodes. *Nanoscale Res Lett* 9:608
35. Manikandan A, Saravanan A, Antony SA, Bououdina M (2015) One-pot low temperature synthesis and characterization studies of nanocrystalline alpha-Fe₂O₃ based dye sensitized solar cells. *J Nanosci Nanotechnol* 15:4358
36. Kong DS, Wang HT, Cha JJ, Pasta M, Koski KJ, Yao J et al (2013) Synthesis of MoS₂ and MoSe₂ films with vertically aligned layers. *Nano Lett* 13:1341
37. Lim J, Kim HA, Kim BH, Han CH, Jun Y (2014) Reversely fabricated dye-sensitized solar cells. *Rsc Adv* 4:243
38. Brito JL, Ilija M, Hernandez P (1995) Thermal and reductive decomposition of ammonium thiomolybdates. *Thermochim Acta* 256:325
39. Dungey KE, Curtis MD, Penner-Hahn JE (1998) Structural characterization and thermal stability of MoS₂ intercalation compounds. *Chem Mater* 10:2152
40. Wang HW, Skeldon P, Thompson GE (1997) XPS studies of MoS₂ formation from ammonium tetrathiomolybdate solutions. *Surf Coat Tech* 91:200
41. Liu CJ, Tai SY, Chou SW, Yu YC, Chang KD, Wang S et al (2012) Facile synthesis of MoS₂/graphene nanocomposite with high catalytic activity toward triiodide reduction in dye-sensitized solar cells. *J Mater Chem* 22:21057
42. Wang HW, Skeldon P, Thompson GE, Wood GC (1997) Synthesis and characterization of molybdenum disulfide formed from ammonium tetrathiomolybdate. *J Mater Sci* 32:497
43. Weber T, Muijsers JC, Niemantsverdriet JW (1995) Structure of amorphous MoS₃. *J Phys Chem-U* 99:9194
44. Gao DQ, Si MS, Li JY, Zhang J, Zhang ZP, Yang ZL et al (2013) Ferromagnetism in freestanding MoS₂ nanosheets. *Nanoscale Res Lett* 8:129
45. Najmaei S, Liu Z, Ajayan PM, Lou J (2012) Thermal effects on the characteristic Raman spectrum of molybdenum disulfide (MoS₂) of varying thicknesses. *Appl Phys Lett* 100:013106

Submit your manuscript to a SpringerOpen® journal and benefit from:

- Convenient online submission
- Rigorous peer review
- Immediate publication on acceptance
- Open access: articles freely available online
- High visibility within the field
- Retaining the copyright to your article

Submit your next manuscript at ► springeropen.com
